

## Applications

- Power Management in Desktop Computer or DC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial.

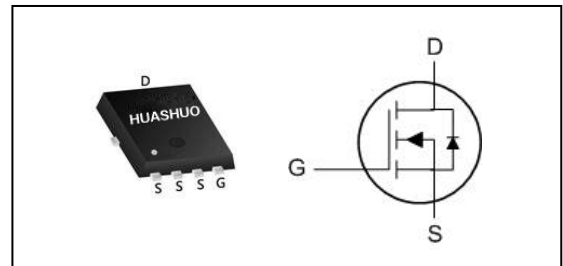
## Features

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density SGT MOS Technology

## Product Summary

$V_{DS}$	30	V
$R_{DS(ON),typ}$	6	m $\Omega$
$I_D$	28	A

## PRPAK3\*3 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	28	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	20	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	100	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	39	mJ
$I_{AS}$	Avalanche Current	28	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	21	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	65	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	6	$^\circ C/W$



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.021	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =12A	---	6	8	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =12A	---	9.4	11	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.7	2.2	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.73	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =12A	---	55	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	0.8	1.7	2.6	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =12A	---	7.1	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2.2	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.1	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω I <sub>D</sub> =12A	---	7	---	ns
T <sub>r</sub>	Rise Time		---	19	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	19.5	---	
T <sub>f</sub>	Fall Time		---	3.4	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	693	---	pF
C <sub>oss</sub>	Output Capacitance		---	332	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	34	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	28	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=28A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.



### Typical Characteristics

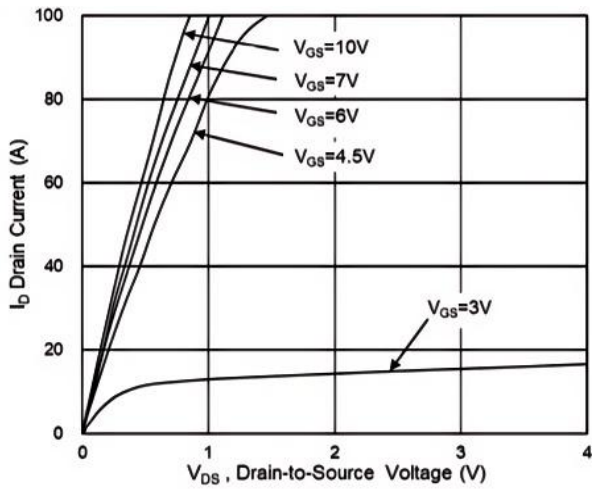


Fig.1 Typical Output Characteristics

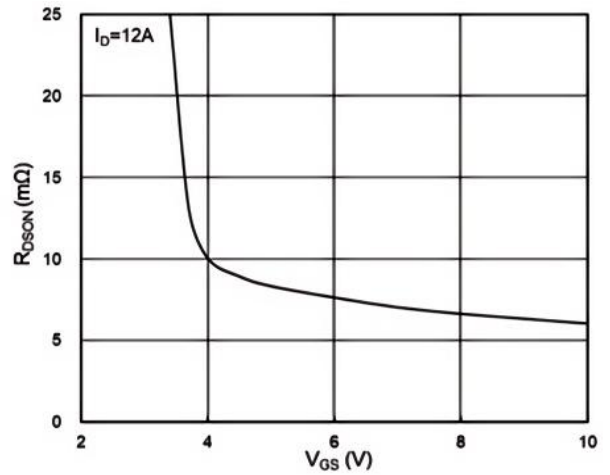


Fig.2 On-Resistance vs. G-S Voltage

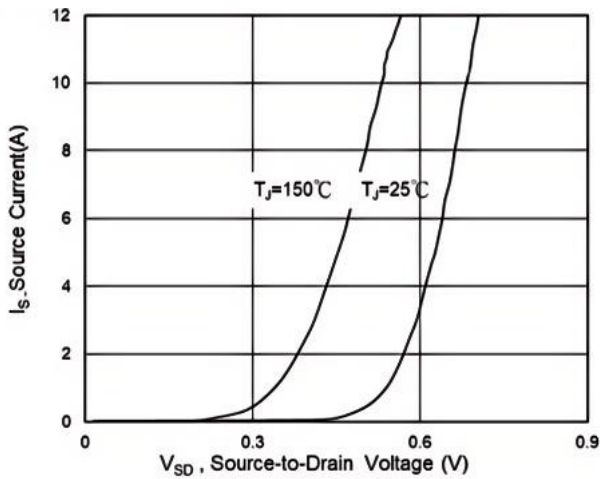


Fig.3 Source Drain Forward Characteristics

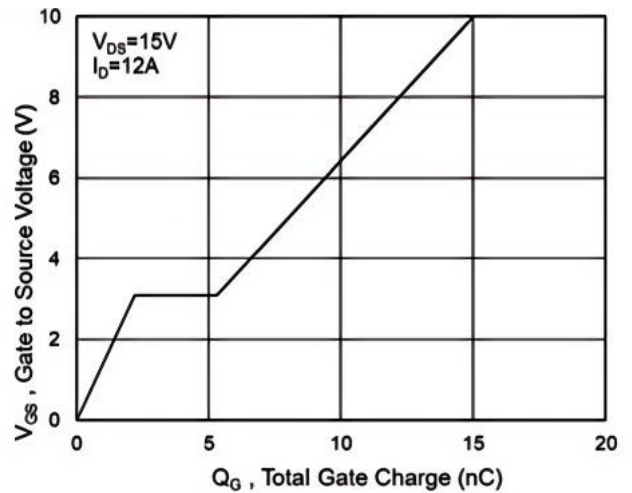


Fig.4 Gate-charge Characteristics

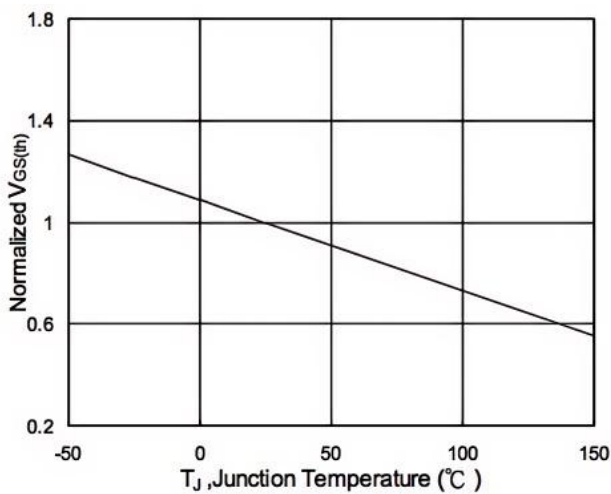


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

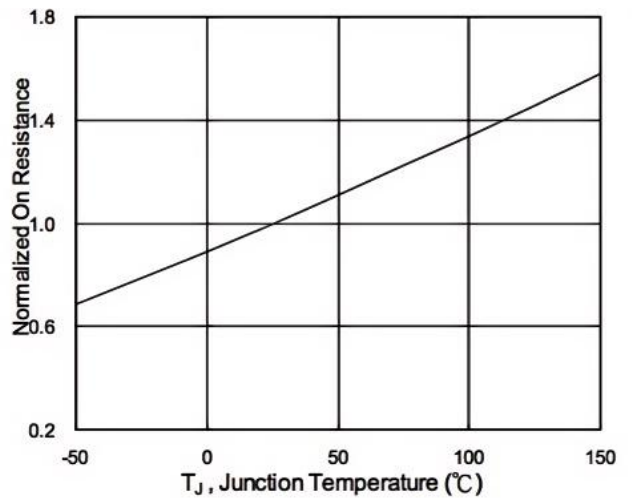
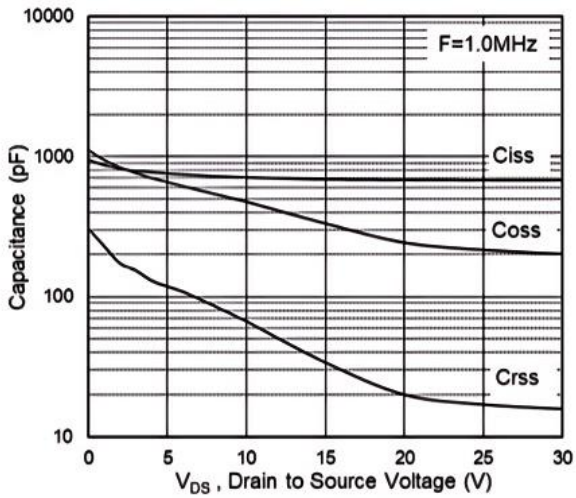
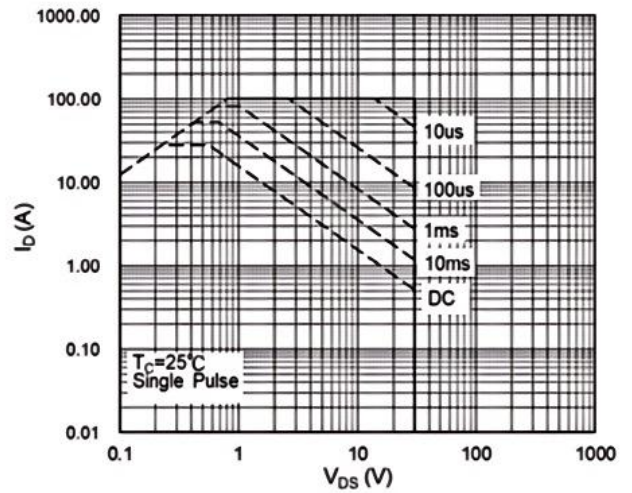


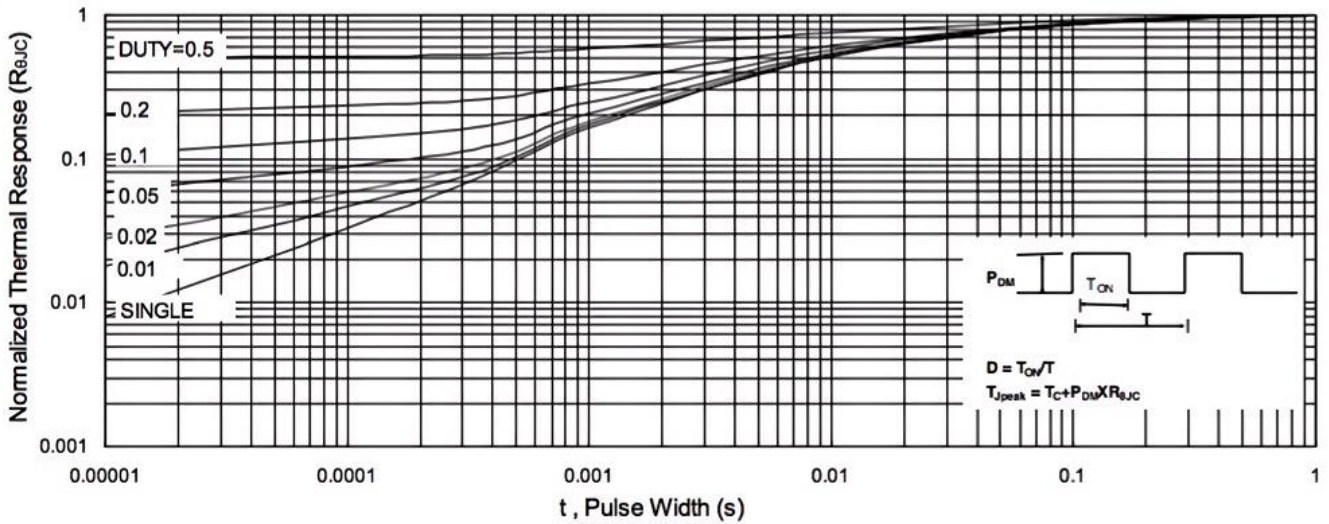
Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$



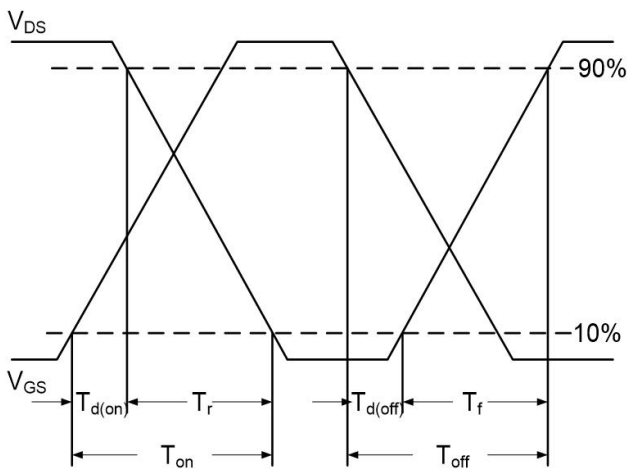
**Fig.7 Capacitance**



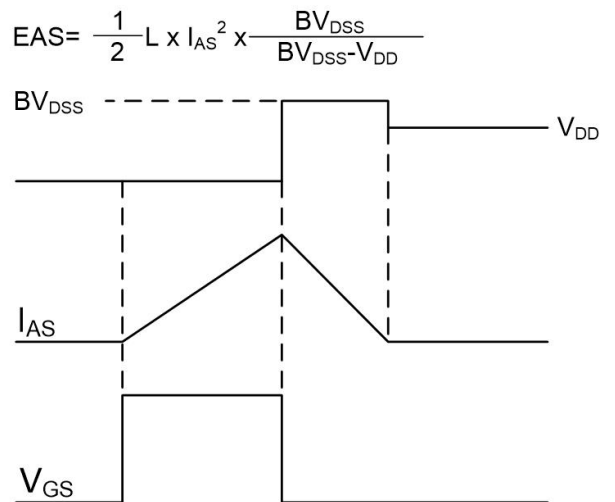
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



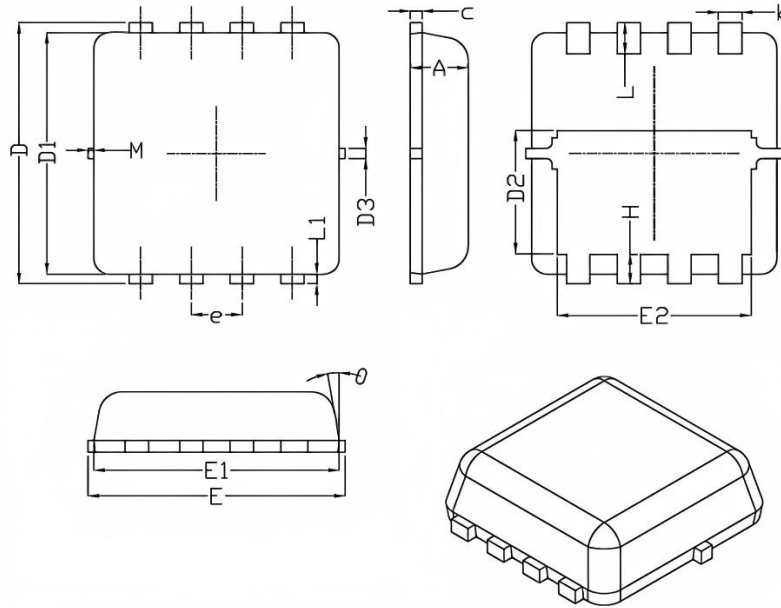
**Fig.11 Unclamped Inductive Switching Waveform**



## Ordering Information

Part Number	Package code	Packaging
HSBB3058	PRPAK3*3	3000/Tape&Reel

**PRPAK3\*3(E) Single Package Outline**



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
C	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.15	3.30	3.45
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°



## HSBB3058 Marking:

